

SPECIFICATIONS:

1. INDUCTANCE: @ 10 kHz, 0.1 Vrms,
1 - 3 > 225 uHy

2. DCR: mOHMS Nom
1 - 3 = 0.1
4 - 6 = 0.1

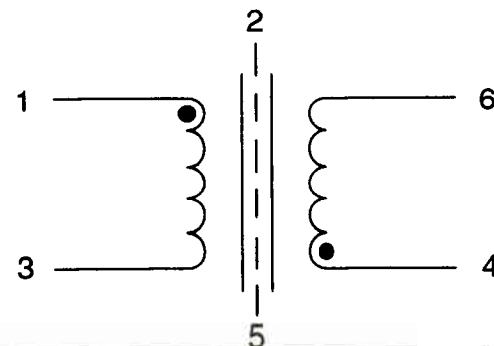
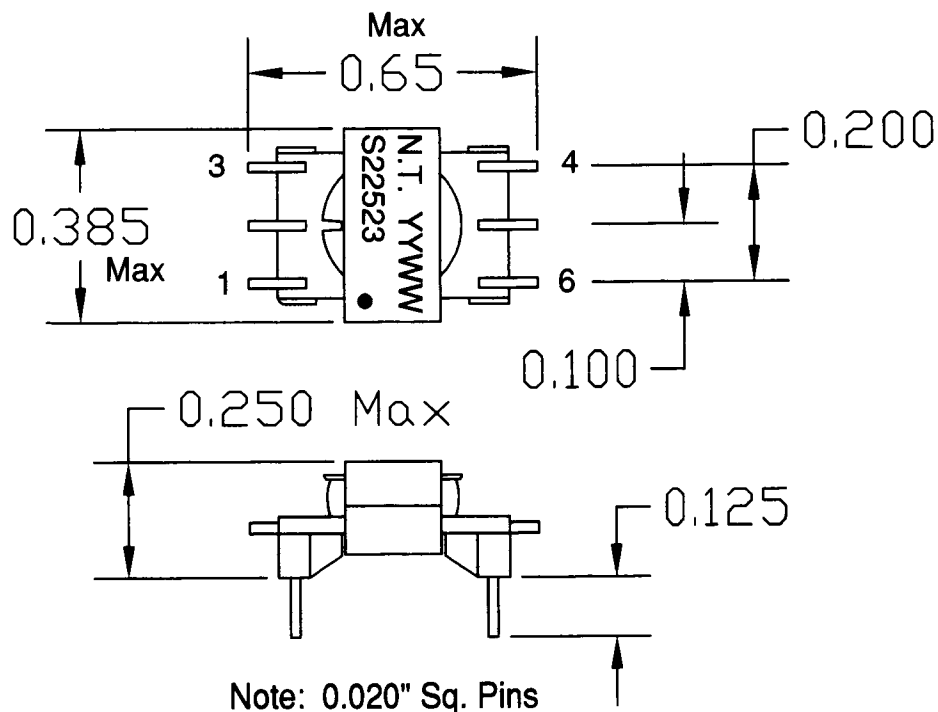
3. LEAKAGE INDUCTANCE: 1 - 3, 1.0 V @ 100kHz
SHORT 4 - 6 < 0.7 uHy

4. INTERWINDING CAPACITANCE: with Shield
Grounded
1 - 3 to 4 - 6 @ 100 KHz, 1.0V < 2.0 pf

5. TURNS AND PHASE:
1 - 3 : 4 - 6 = 1 : 1.22 +/- 2%

6 DIELECTRIC STRENGTH:
1500 VAC 1 sec

Note: Designed to operate with Crystal Semiconductor
CS8401.8402, 8411 & 8412



A	REV.	DATE	ECN	BY	DESCRIPTION			
					TOLERANCES ON			
					.XXX	.XX	ANGLE	
					± -	± -	± -	
							DATE	
					DRAWN:		SCALE	MODEL
					CHECKED: -	-		
					APPROVED: -	-	NEXT ASSY:	
					THIS PRINT MUST NOT BE COPIED IN WHOLE OR IN PART OR USED DETRIMENTALLY TO OUR INTEREST			
					SHEET 1 OF 1			

Newava Tech.
Watertown, SD 57201
605-886-0264

Transformer
Power, 1:1.22

DRAWING NO.

REV.

S22523

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